1A, 600V Hyperfast Diode

The RHR1K160 is a hyperfast diode with soft recovery characteristics (t_{rr} < 25ns). It has half the recovery time of ultrafast diodes and is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.
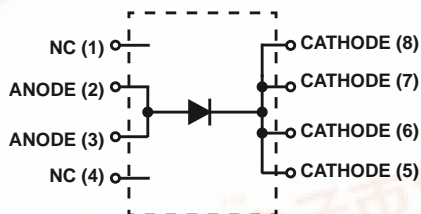
Formerly developmental type TA49185.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHR1K160	MS-012AA	RHR1K160

NOTE: When ordering, use the entire part number. For ordering in tape and reel, add the suffix 96 to the part number, i.e. RHR1K16096.

Symbol

Features

- Hyperfast with Soft Recovery . . . .<25ns
- Operating Temperature. . . . . .150°C
- Reverse Voltage 600V
- *Thermal Impedance* SPICE Model
- *Thermal Impedance* SABER™ Model
- Avalanche Energy Rated
- Planar Construction
- Related Literature
  - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC MS-012AA
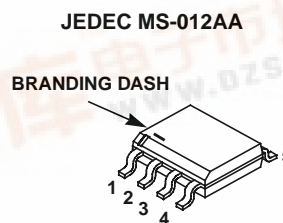
Absolute Maximum Ratings T_A = 25°C, Unless Otherwise Specified

		RHR1K160	UNITS
Peak Repetitive Reverse Voltage.	V_{RRM}	600	V
Working Peak Reverse Voltage	V_{RWM}	600	V
DC Blocking Voltage	V_R	600	V
Average Rectified Forward Current . . . . T_A = 65°C	$I_{F(AV)}$	1	A
Repetitive Peak Surge Current . . . . Square Wave, 20kHz	I_{FRM}	2	A
Nonrepetitive Peak Surge Current . . . . Halfwave, 1 Phase, 60Hz	I_{FSM}	10	A
Maximum Power Dissipation (Note 1)	P_D	2.5	W
Avalanche Energy (See Figures 11 and 12)	E_{AVL}	5	mJ
Operating and Storage Temperature	T_{STG}, T_J	-55 to 150	^{o}C
Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10s.	T_L	300	^{o}C
Package Body for 10s, See Tech brief 334	T_{pkg}	260	^{o}C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Specifications $T_A = 25^oC$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V_F	$I_F = 1A$	-	-	2.1	V
	$I_F = 1A, T_A = 150^oC$	-	-	1.7	V
I_R	$V_R = 600V$	-	-	100	μA
	$V_R = 600V, T_A = 150^oC$	-	-	500	μA
t_{rr}	$I_F = 1A, dI_F/dt = 200A/μs$	-	-	25	ns
t_a	$I_F = 1A, dI_F/dt = 200A/μs$	-	10.5	-	ns
t_b	$I_F = 1A, dI_F/dt = 200A/μs$	-	5	-	ns
Q_{RR}	$I_F = 1A, dI_F/dt = 200A/μs$	-	20	-	nC
C_J	$V_R = 10V, I_F = 0A$	-	10	-	pF
$R_{θJA}$	Pad Area = 0.769 in^2 (Note 1)	-	-	50	$^oC/W$
	Pad Area = 0.054 in^2 (Note 2) (Figure 13)	-	-	177	$^oC/W$
	Pad Area = 0.0115 in^2 (Note 2) (Figure 13)	-	-	217	$^oC/W$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300μs, D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 10), summation of t_a + t_b.

t_a = Time to reach peak reverse current (See Figure 10).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 10).

Q_{rr} = Reverse recovery charge.

C_J = Junction Capacitance.

$R_{θJA}$ = Thermal resistance junction to ambient.

pw = Pulse width.

D = Duty cycle.

NOTES:

1. Measured using FR-4 copper board at 3.2 seconds.

2. Measured using FR-4 copper board at 1000 seconds.

Typical Performance Curves
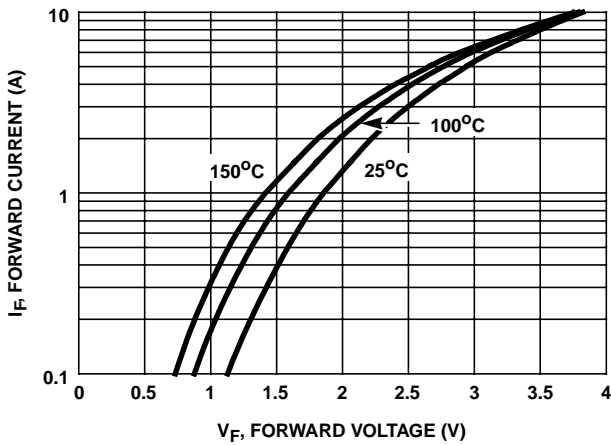
FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE
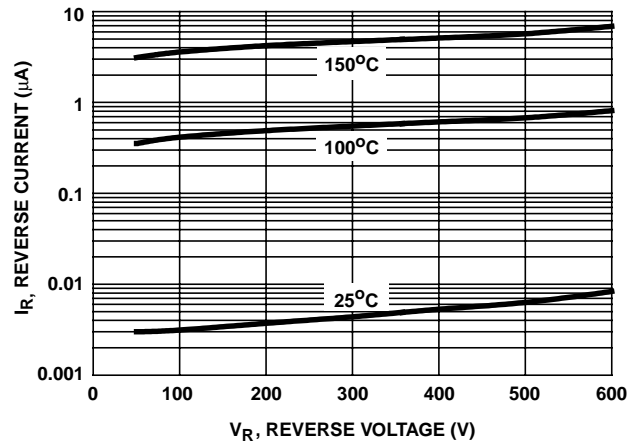
FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE
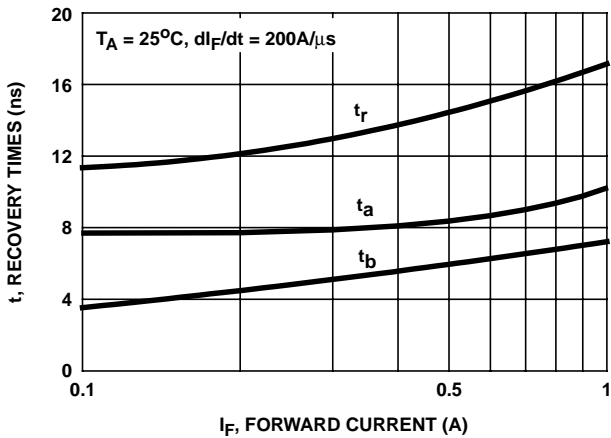
FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT
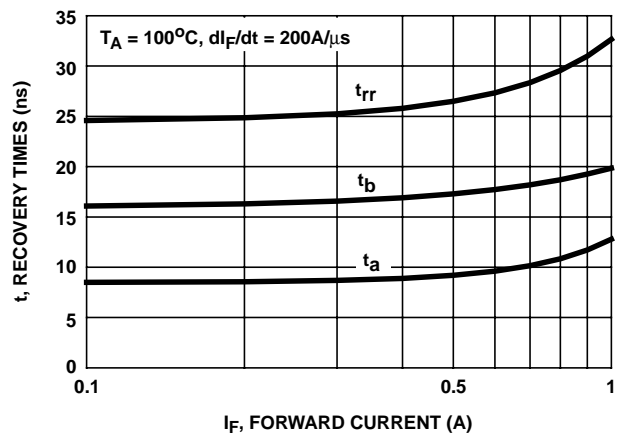
FIGURE 4. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT
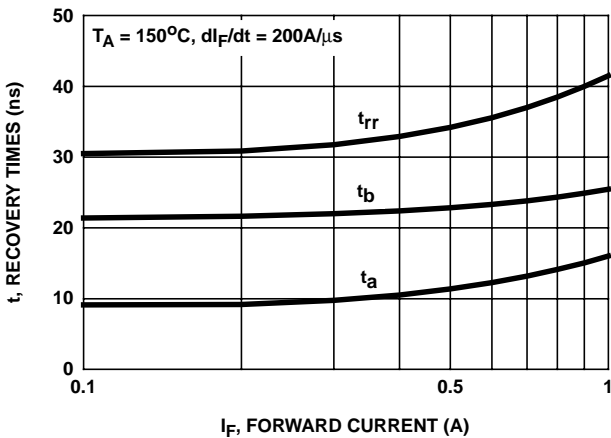
FIGURE 5. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT
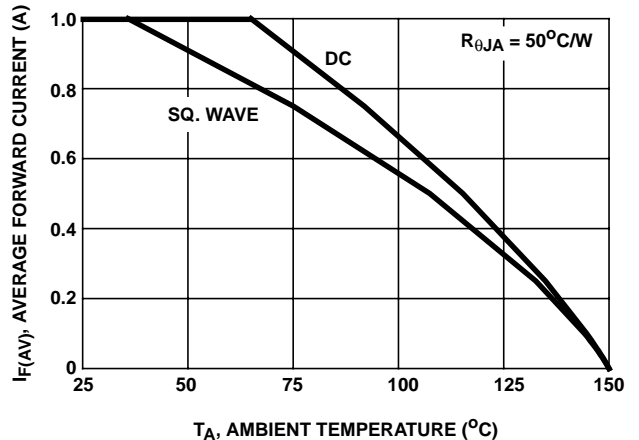
FIGURE 6. CURRENT DERATING CURVE

Typical Performance Curves (Continued)
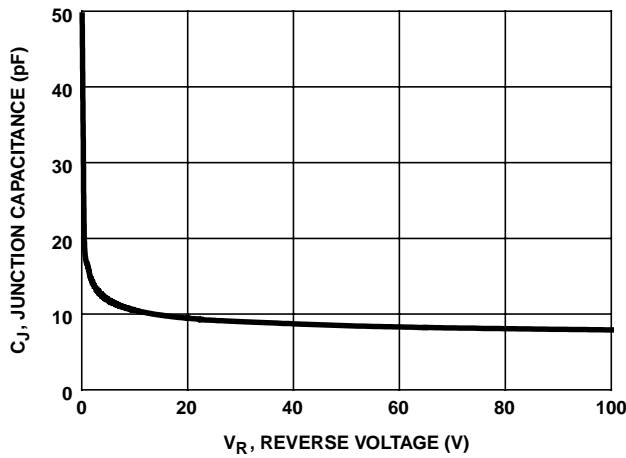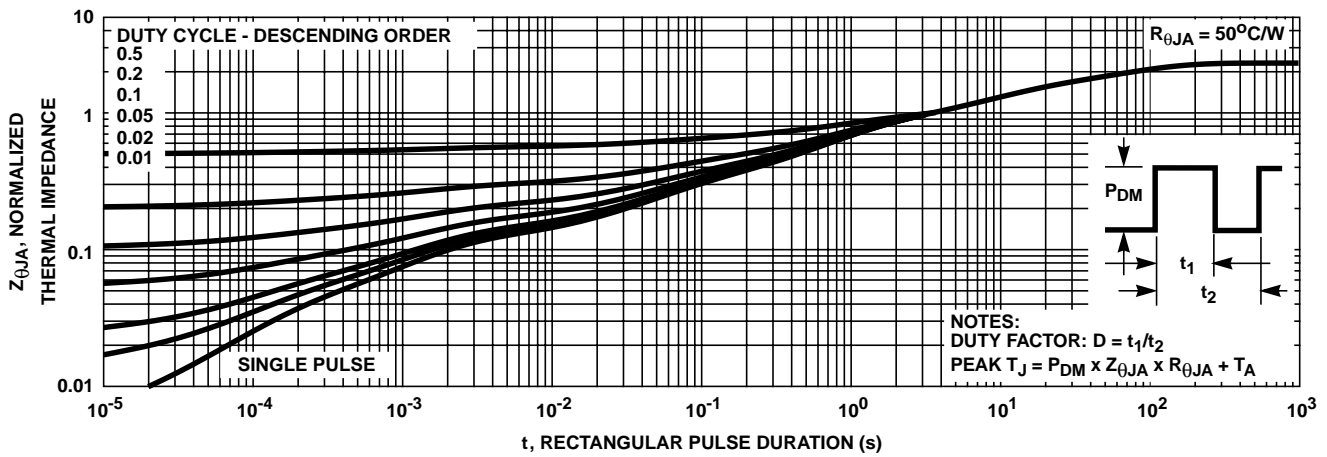

FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

FIGURE 8. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

Test Circuits and Waveforms
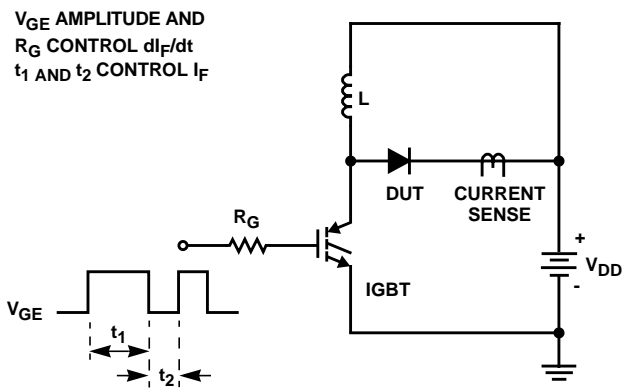
FIGURE 9. t_{rr} TEST CIRCUIT

FIGURE 10. t_{rr} WAVEFORMS AND DEFINITIONS

The transient thermal impedance ($Z_{\theta JA}$) is also effected by various top copper board areas. Figure 14 shows the effect of copper pad area on the single pulse transient thermal impedance. Each trace represents a copper pad area in square inches corresponding to the descending list in the graph. Spice and SABER thermal models are provided for each of the listed pad areas.

Copper pad area has no perceivable effect on transient thermal impedance for pulse widths less than 100ms. For pulse widths less than 100ms the transient thermal impedance is determined by the die and package. Therefore, CTHERM1 through CTHERM5 and RTHERM1 through RTHERM4 remain constant for each of the thermal models. A listing of the model component values is available in Table 1.
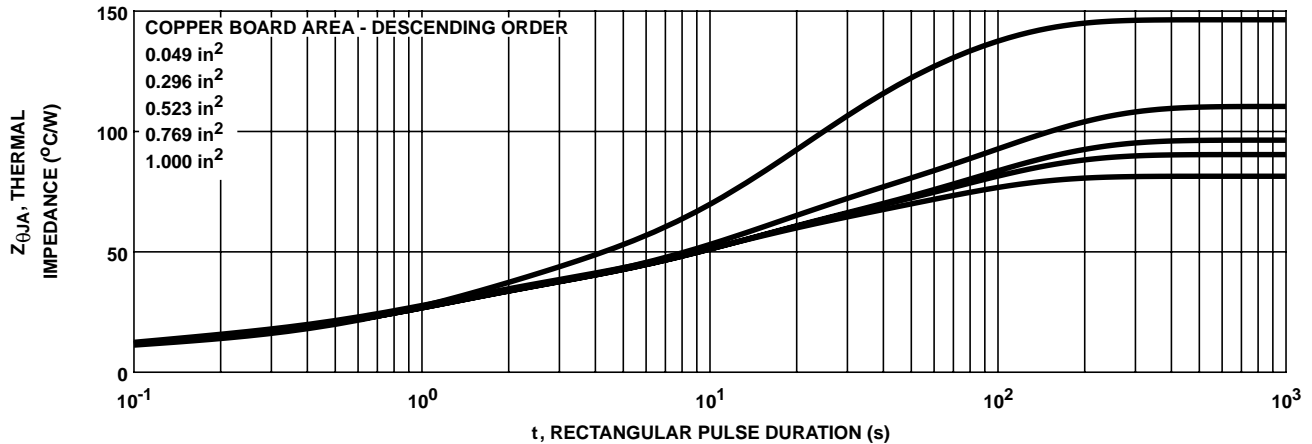

FIGURE 14. TRANSIENT THERMAL IMPEDANCE vs MOUNTING PAD AREA

SPICE Thermal Model

REV August 1998

RHR1K160

Copper Area = 0.769 in^2

CTHERM1 th 8 5e-6
CTHERM2 8 7 2.5e-5
CTHERM3 7 6 1.2e-4
CTHERM4 6 5 4.5e-4
CTHERM5 5 4 9e-3
CTHERM6 4 3 4.5e-2
CTHERM7 3 2 3.5e-1
CTHERM8 2 tl 2

RTHERM1 th 8 4e-2
RTHERM2 8 7 1.6e-1
RTHERM3 7 6 1
RTHERM4 6 5 3.2
RTHERM5 5 4 6
RTHERM6 4 3 19
RTHERM7 3 2 25
RTHERM8 2 tl 36

SABER Thermal Model

Copper Area = 0.769 in^2

template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th 8 = 5e-6
ctherm.ctherm2 8 7 = 2.5e-5
ctherm.ctherm3 7 6 = 1.2e-4
ctherm.ctherm4 6 5 = 4.5e-4
ctherm.ctherm5 5 4 = 9e-3
ctherm.ctherm6 4 3 = 4.5e-2
ctherm.ctherm7 3 2 = 3.5e-1
ctherm.ctherm8 2 tl = 2

rtherm.rtherm1 th 8 = 4e-2
rtherm.rtherm2 8 7 = 1.6e-1
rtherm.rtherm3 7 6 = 1
rtherm.rtherm4 6 5 = 3.2
rtherm.rtherm5 5 4 = 6
rtherm.rtherm6 4 3 = 19
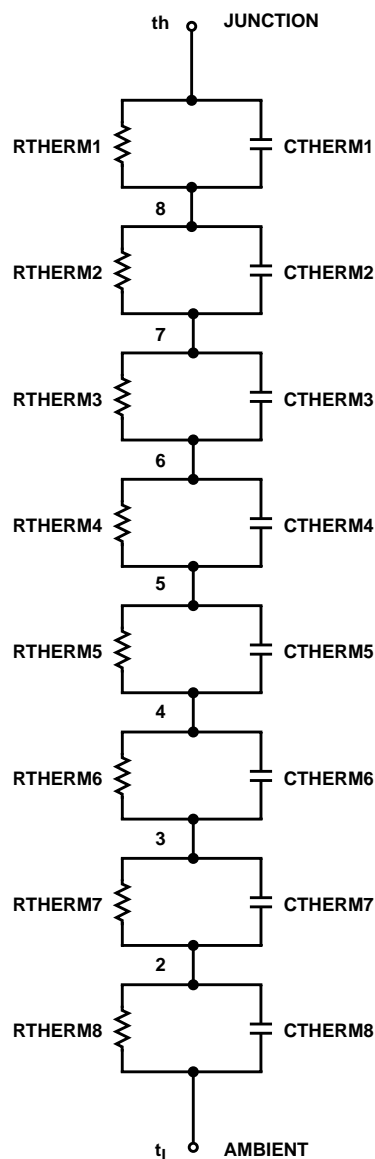rtherm.rtherm7 3 2 = 25
rtherm.rtherm8 2 tl = 36
}

TABLE 1. THERMAL MODELS

COMPONENT	0.049 in^2	0.296 in^2	0.523 in^2	0.769 in^2	1.0 in^2
CTHERM6	5e-2	4.5e-2	4.5e-2	4.5e-2	4.5e-2
CTHERM7	2.5e-1	3.5e-1	3.5e-1	3.5e-1	3.5e-1
CTHERM8	1	2	2	2	2
RTHERM5	5	6	6	6	7
RTHERM6	22	19	19	19	19
RTHERM7	60	32	25	25	23
RTHERM8	55	49	42	36	28

All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.
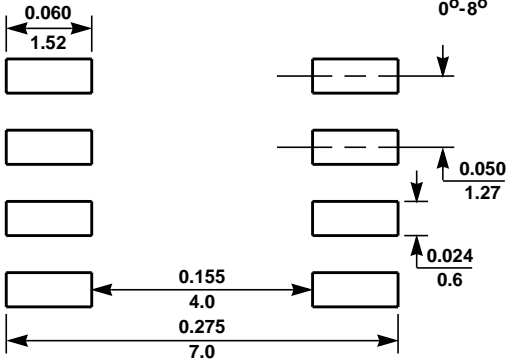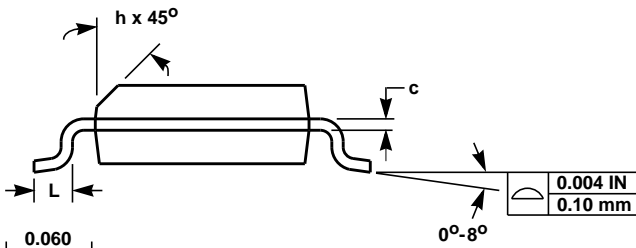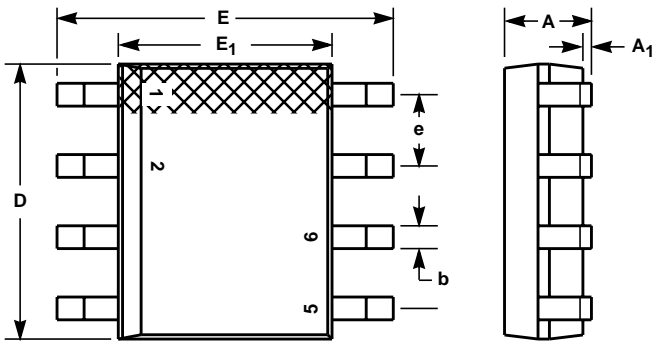
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MS-012AA

**8 LEAD JEDEC MS-012AA SMALL OUTLINE PLASTIC PACKAGE**

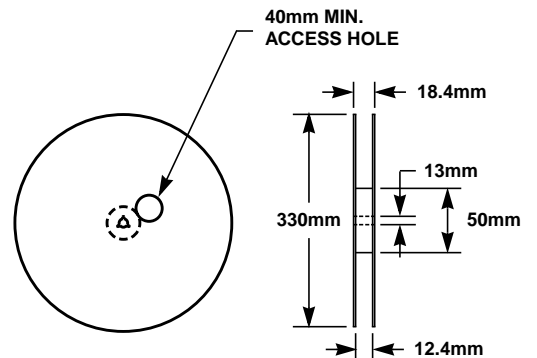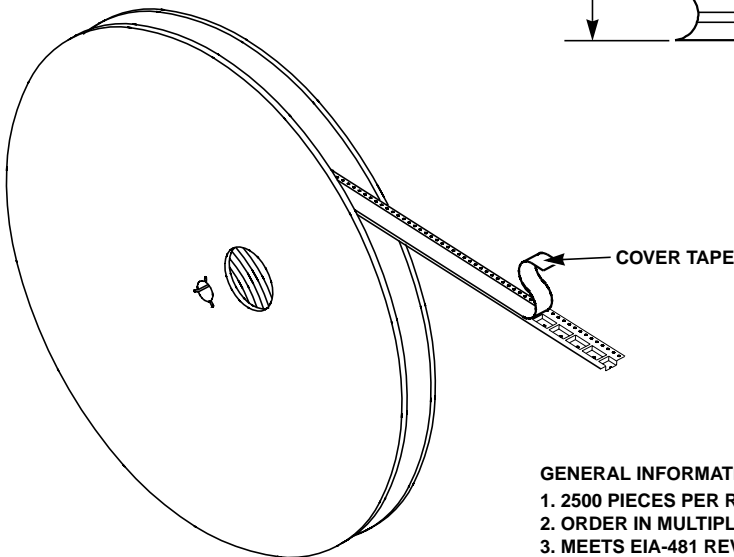| SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.0532	0.0688	1.35	1.75	-
A₁	0.004	0.0098	0.10	0.25	-
b	0.013	0.020	0.33	0.51	-
c	0.0075	0.0098	0.19	0.25	-
D	0.189	0.1968	4.80	5.00	2
E	0.2284	0.244	5.80	6.20	-
E₁	0.1497	0.1574	3.80	4.00	3
e	0.050 BSC		1.27 BSC		-
H	0.0099	0.0196	0.25	0.50	-
L	0.016	0.050	0.40	1.27	4

NOTES:

1. All dimensions are within allowable dimensions of Rev. C of JEDEC MS-012AA outline dated 5-90.

2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.006 inches (0.15mm) per side.

3. Dimension "E₁" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 0.010 inches (0.25mm) per side.

4. "L" is the length of terminal for soldering.

5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.

6. Controlling dimension: Millimeter.

7. Revision 8 dated 5-99.

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE-MOUNTED APPLICATIONS
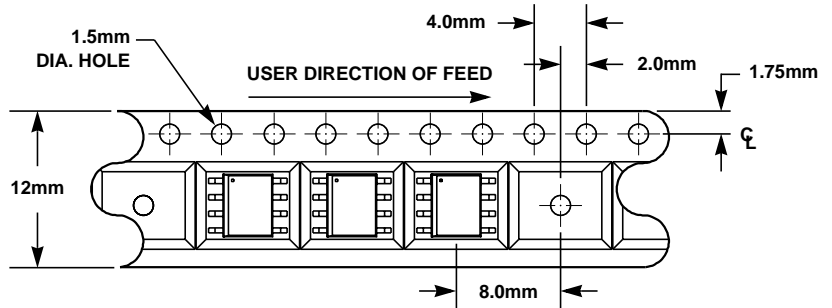
MS-012AA

12mm TAPE AND REEL

COVER TAPE

40mm MIN. ACCESS HOLE

GENERAL INFORMATION
1. 2500 PIECES PER REEL.
2. ORDER IN MULTIPLES OF FULL REELS ONLY.
3. MEETS EIA-481 REVISION "A" SPECIFICATIONS.